

SWITCHING REGULATOR APPLICATIONS

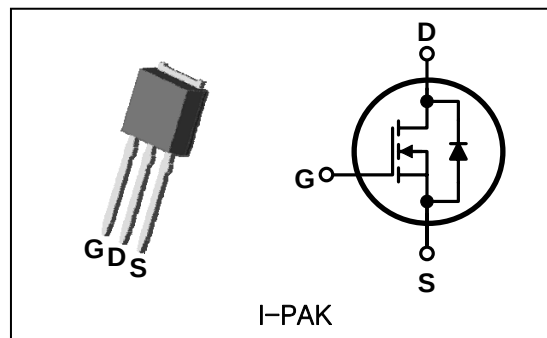
Features

- High Voltage : $BV_{DSS}=600V(\text{Min.})$
- Low C_{RSS} : $C_{RSS}=3.4pF(\text{Typ.})$
- Low gate charge : $Q_g=3.9nC(\text{Typ.})$
- Low $R_{DS(on)}$: $R_{DS(on)}=11.5\Omega(\text{Max.})$

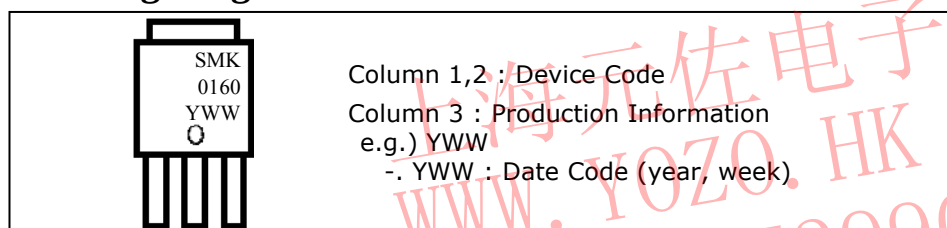
Ordering Information

Type No.	Marking	Package Code
SMK0160I	SMK0160	I-PAK

PIN Connection



Marking Diagram



Absolute maximum ratings ($T_C=25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Rating	Unit
Drain-source voltage	V_{DSS}	600	V
Gate-source voltage	V_{GSS}	± 30	V
Drain current (DC) *	I_D	($T_C=25^\circ\text{C}$)	1.0
		($T_C=100^\circ\text{C}$)	0.77
Drain current (Pulsed) *	I_{DM}	4.0	A
Power dissipation	P_D	28	W
Avalanche current (Single) ②	I_{AS}	1.0	A
Single pulsed avalanche energy ②	E_{AS}	22	mJ
Avalanche current (Repetitive) ①	I_{AR}	1.0	A
Repetitive avalanche energy ①	E_{AR}	2.5	mJ
Junction temperature	T_J	150	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55~150	

* Limited by maximum junction temperature

Characteristic	Symbol	Typ.	Max.	Unit
Thermal resistance	Junction-case	$R_{th(J-C)}$	-	4.46
	Junction-ambient	$R_{th(J-A)}$	-	62.5

Electrical Characteristics (T_C=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Drain-source breakdown voltage	BV _{DSS}	I _D =250uA, V _{GS} =0	600	-	-	V
Gate threshold voltage	V _{GS(th)}	I _D =250uA, V _{DS} =V _{GS}	2.0	-	4.0	V
Drain-source cut-off current	I _{DSS}	V _{DS} =600V, V _{GS} =0V	-	-	1	uA
Gate leakage current	I _{GSS}	V _{DS} =0V, V _{GS} =±30V	-	-	±100	nA
Drain-source on-resistance ④	R _{DS(ON)}	V _{GS} =10V, I _D =0.5A	-	9.3	11.5	Ω
Forward transfer conductance ④	g _{fs}	V _{DS} =10V, I _D =0.5A	-	0.32	-	S
Input capacitance	C _{iss}	V _{GS} =0V, V _{DS} =25V, f=1MHz	-	131	164	pF
Output capacitance	C _{oss}		-	19.4	24.3	
Reverse transfer capacitance	C _{rss}		-	3.4	4.3	
Turn-on delay time	t _{d(on)}	V _{DD} =300V, I _D =1.0A R _G =25Ω ③④	-	5.5	-	ns
Rise time	t _r		-	5	-	
Turn-off delay time	t _{d(off)}		-	13	-	
Fall time	t _f		-	28	-	
Total gate charge	Q _g	V _{DS} =480V, V _{GS} =10V I _D =1.0A ③④	-	3.9	4.9	nC
Gate-source charge	Q _{gs}		-	1.7	-	
Gate-drain charge	Q _{gd}		-	0.85	-	

Source-Drain Diode Ratings and Characteristics (T_C=25°C unless otherwise noted)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Source current (DC)	I _S	Integral reverse diode in the MOSFET	-	-	1.0	A
Source current (Pulsed) ①	I _{SM}		-	-	4.0	
Forward voltage ④	V _{SD}	V _{GS} =0V, I _S =1.0A	-	-	1.4	V
Reverse recovery time	t _{rr}	I _S =1.0A, V _{GS} =0V dI _F /dt=100A/us	-	190	-	ns
Reverse recovery charge	Q _{rr}		-	0.53	-	uC

Note ;

- ① Repetitive rating : Pulse width limited by maximum junction temperature
- ② L=1080mH, I_{AS}=0.3A, V_{DD}=50V, R_G=25Ω, Starting T_J=25°C
- ③ Pulse Test : Pulse width≤300us, Duty cycle≤2%
- ④ Essentially independent of operating temperature

Electrical Characteristic Curves

Fig. 1 $I_D - V_{DS}$

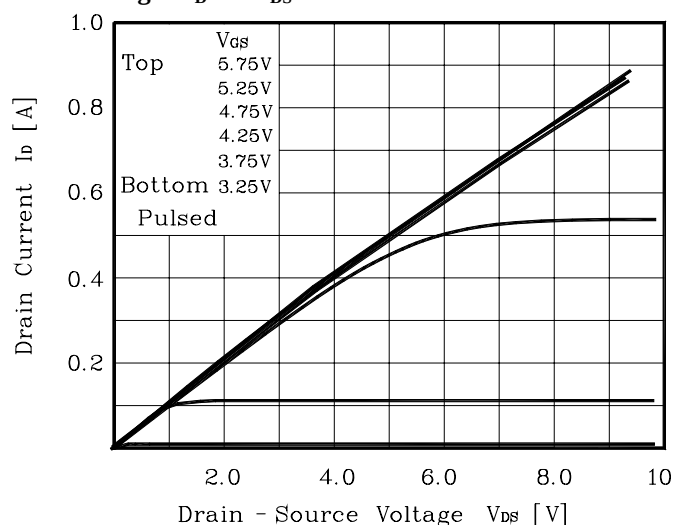


Fig. 2 $I_D - V_{GS}$

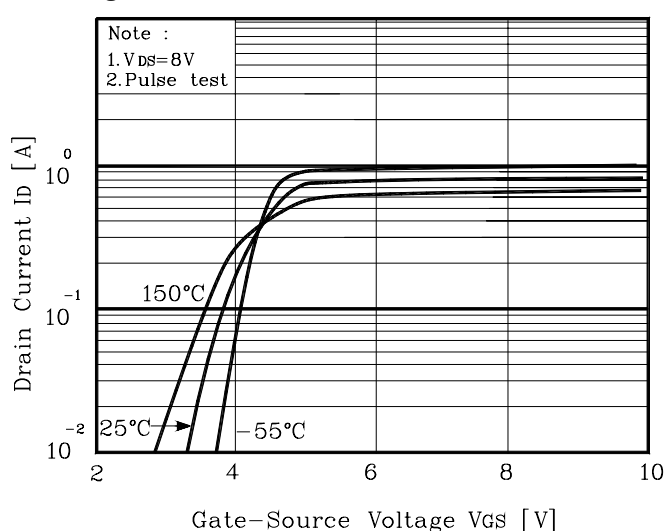


Fig. 3 $R_{DS(on)} - I_D$

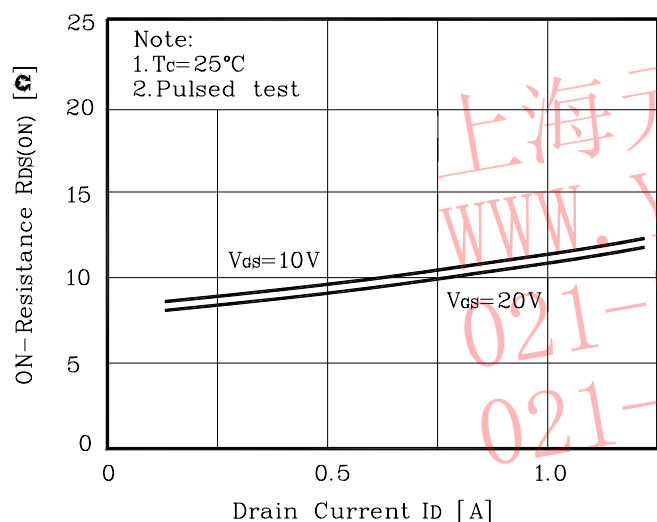


Fig. 4 $I_S - V_{SD}$

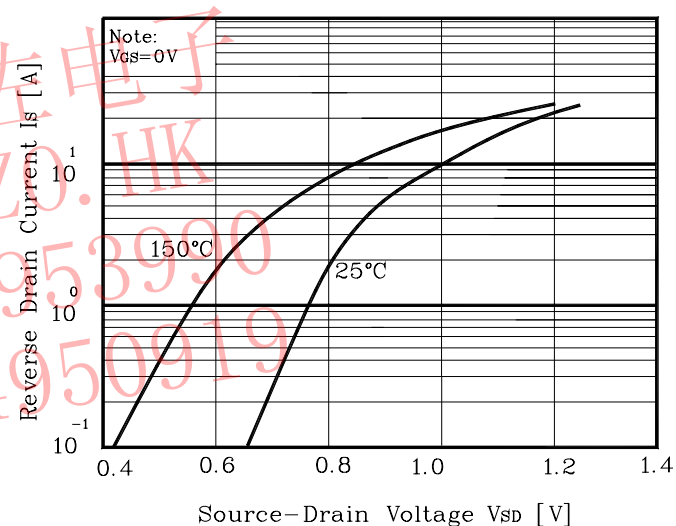


Fig. 5 Capacitance - V_{DS}

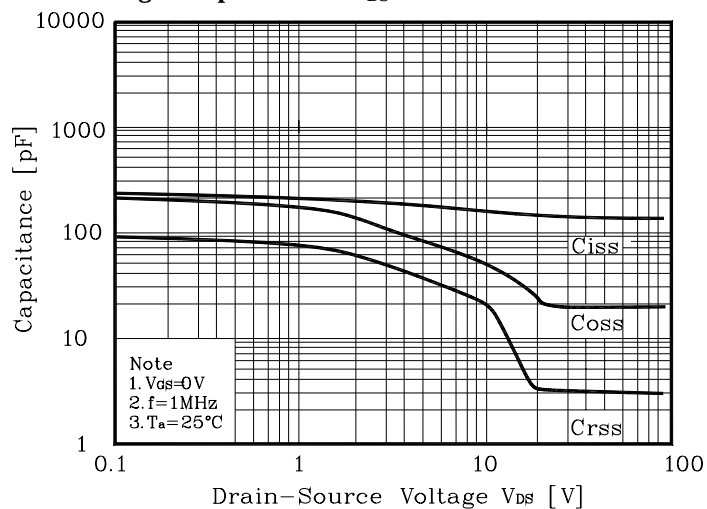


Fig. 6 $V_{GS} - Q_G$

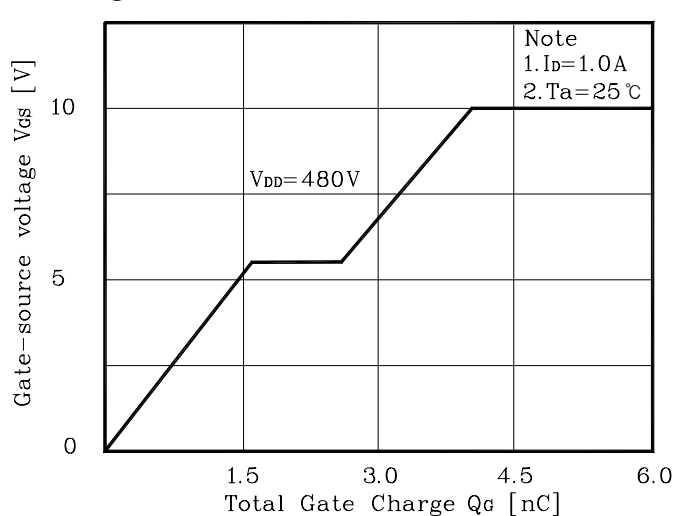


Fig. 7 $V_{DS} - T_J$

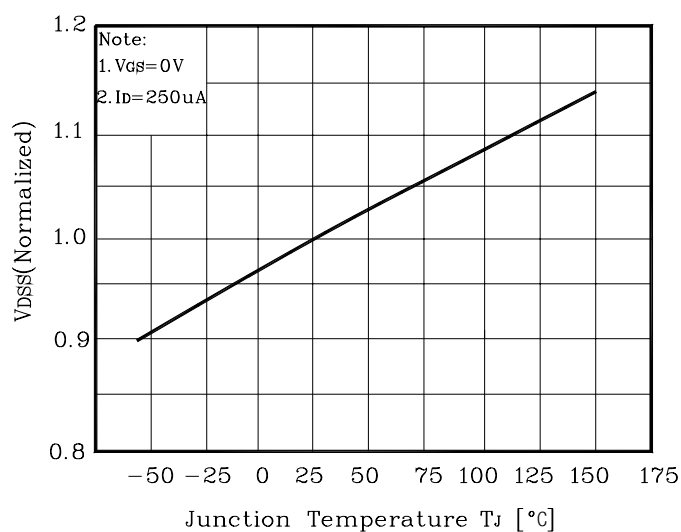


Fig. 8 $R_{DS(on)} - T_J$

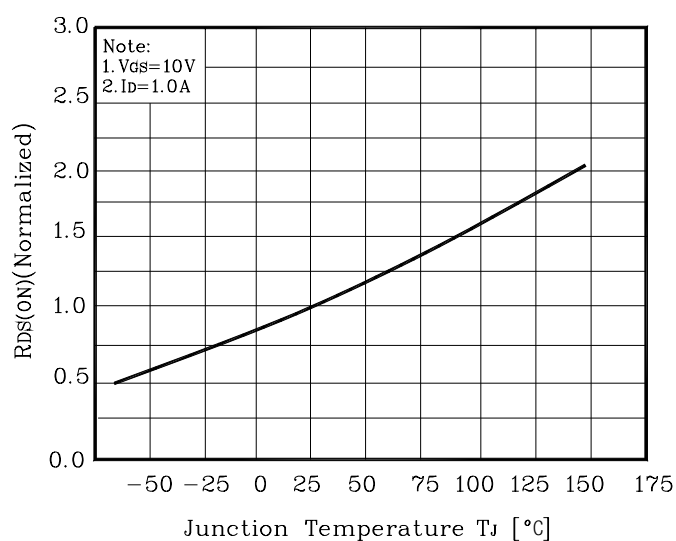


Fig. 9 $I_D - T_a$

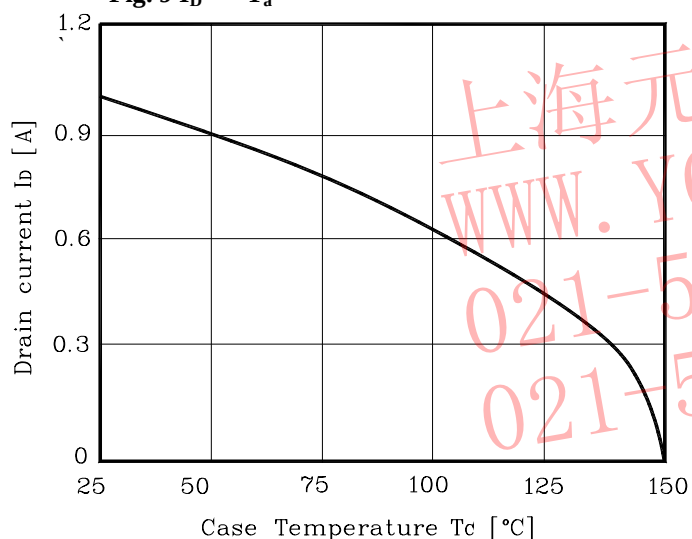


Fig. 10 Safe Operating Area

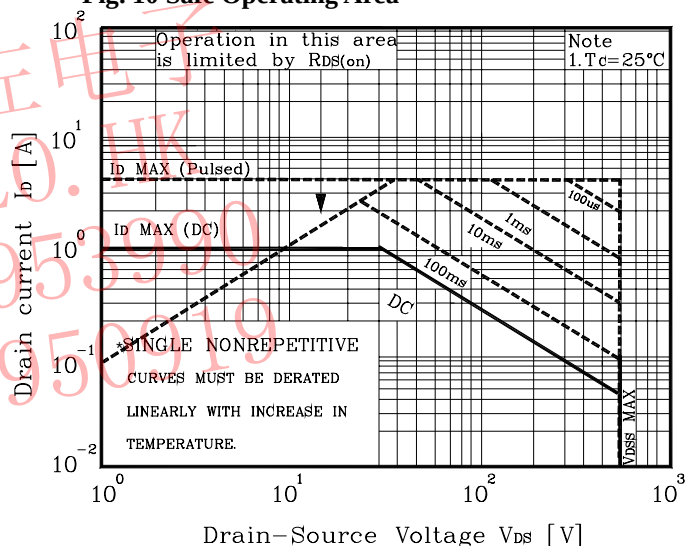


Fig. 11 Gate Charge Test Circuit & Waveform

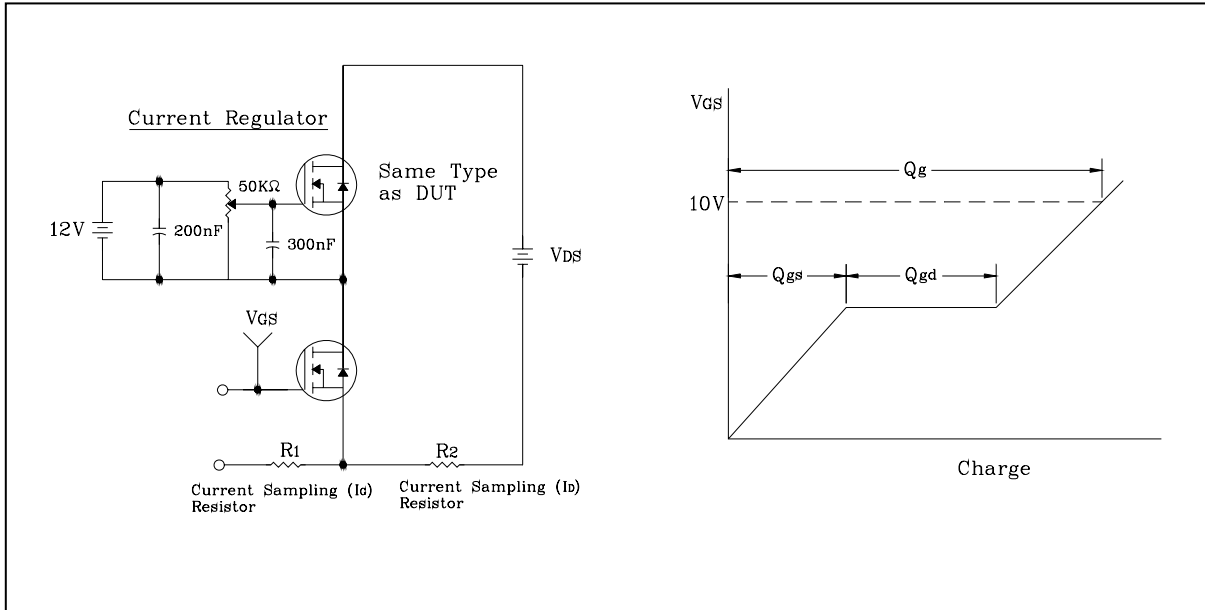


Fig. 12 Resistive Switching Test Circuit & Waveform

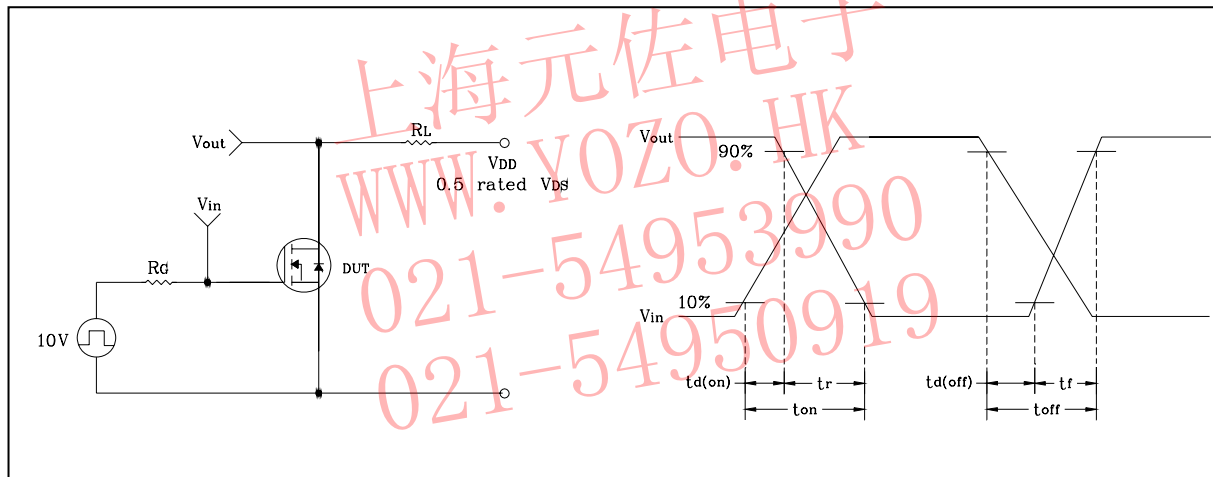


Fig. 13 EAS Test Circuit & Waveform

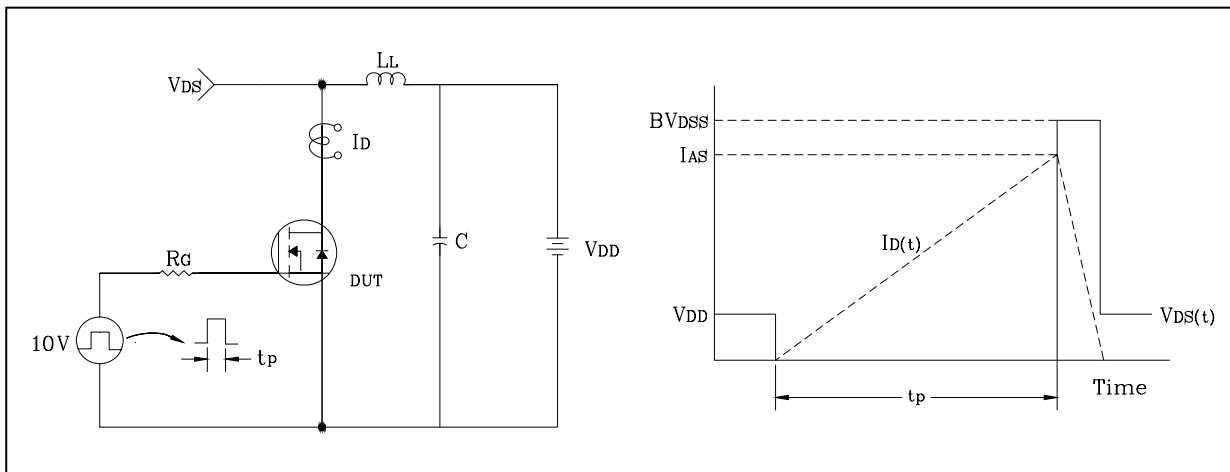
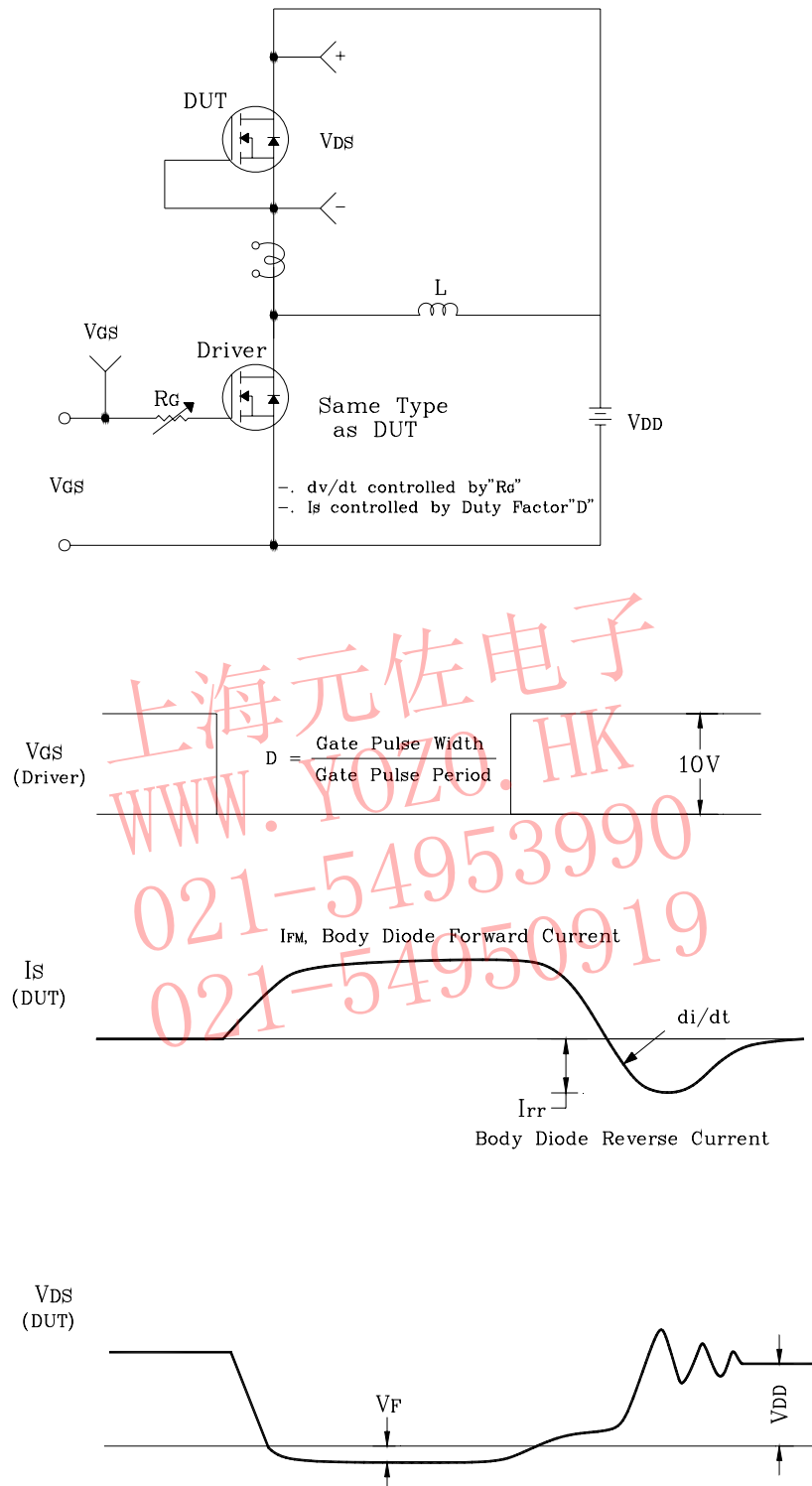
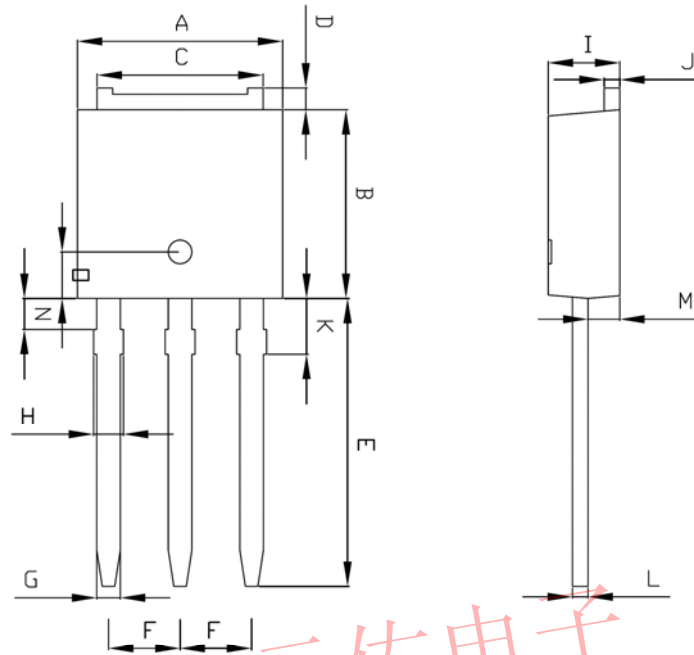


Fig. 14 Diode Reverse Recovery Time Test Circuit & Waveform



Outline Dimension

unit: mm



SYMBOL	MILLIMETERS			NOTE
	MINIMUM	NOMINAL	MAXIMUM	
A	6.40	6.60	6.80	
B	5.90	6.10	6.30	
C	5.04	5.34	5.64	
D	0.50	0.70	0.90	
E	9.00	9.30	9.60	
F	2.10	2.30	2.50	
G	0.66	0.76	0.86	
H	0.96 MAX			
I	2.20	2.30	2.40	
J	0.40	0.50	0.60	
K	1.60	1.80	2.00	
L	0.40	0.50	0.60	
M	0.72	1.02	1.32	
N	0.90	1.00	1.10	
O	1.50			